

## **KSC5042M**

## **High Voltage Switching Dynamic Focus Application**

- High Collector-Emitter Breakdown Voltage :  $BV_{CEO}$ =900V
- Small C<sub>ob</sub> =2.8pF (Typ.)
  Wide S.O.A
- · High reliability



# **NPN Triple Diffused Planar Silicon Transistor**

## **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	900	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	100	mA
I <sub>CP</sub>	Collector Current (Pulse)	300	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	4	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

## Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1 \text{ mA}, I_E = 0$	1500			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	900			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 900V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			10	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 10mA$	30			
V <sub>CE (sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 20$ mA, $I_B = 4$ mA			5	V
V <sub>BE (sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 20$ mA, $I_B = 4$ mA			2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 100V, f = 1MHz		2.8		pF

## **Typical Characteristics**

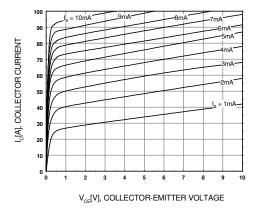


Figure 1. Static Characteristic

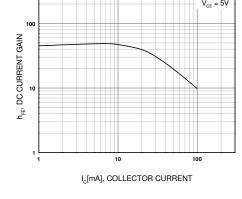


Figure 2. DC current Gain

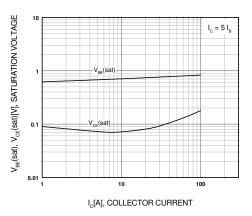


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

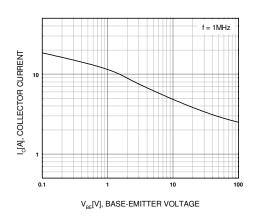


Figure 4. Collector-Base Capacitance

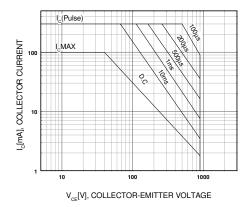


Figure 5. Safe Operating Area

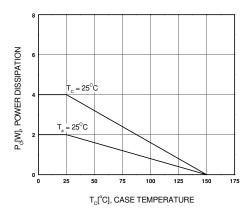
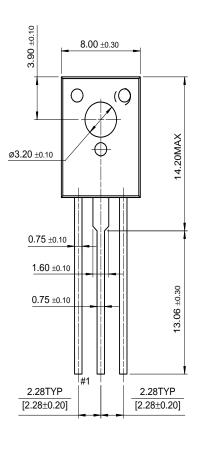


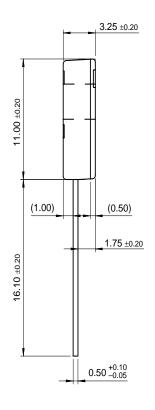
Figure 6. Power Derating

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# **Package Dimensions**

TO-126







Dimensions in Millimeters

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EnSigna™	I <sup>2</sup> C <sup>TM</sup>	OCX™	RapidConfigure™	UHC™
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The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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